

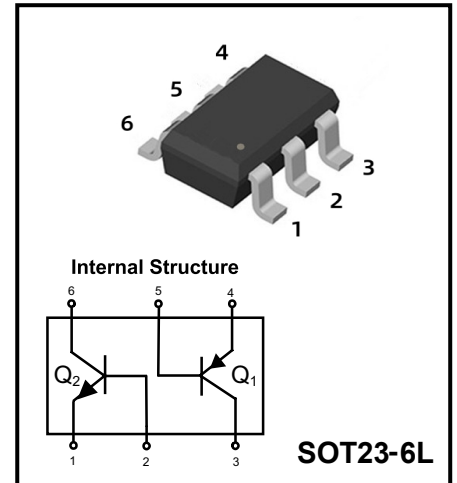
Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+PNP)

FEATURES

- ◆ Complementary Pair
- ◆ One 3904-Type NPN
One 3906-Type PNP
- ◆ Epitaxial Planar Die Construction
- ◆ Ideal for Low Power Amplification and Switching

Marking Code	
MMDT3946F	K46



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.2	A
P_C	Collector Power Dissipation	0.3	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

NPN 3904 ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 30V, I_E = 0$		0.05	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 30V, I_B = 0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1V, I_C = 0.1mA$	40		
	$h_{FE(2)}$	$V_{CE} = 1V, I_C = 1mA$	70		
	$h_{FE(3)}$	$V_{CE} = 1V, I_C = 10mA$	100	300	
	$h_{FE(4)}$	$V_{CE} = 1V, I_C = 50mA$	60		
	$h_{FE(5)}$	$V_{CE} = 1V, I_C = 100mA$	30		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = 10mA, I_B = 1mA$		0.2	V
	$V_{CE(sat)2}$	$I_C = 50mA, I_B = 5mA$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C = 10mA, I_B = 1mA$	0.65	0.85	V
	$V_{BE(sat)2}$	$I_C = 50mA, I_B = 5mA$		0.95	V
Transition frequency	f_T	$V_{CE} = 20V, I_C = 20mA, f = 100MHz$	300		MHz
Noise figure	NF	$V_{CE} = 5V, I_C = 0.1mA, f = 1KHz, R_g = 1K\Omega$		5	dB
Output capacitance	C_{ob}	$V_{CB} = 5V, I_E = 0, f = 1MHz$		4	pF
Delay time	t_d	$V_{CC} = 3V, V_{BE} = 0.5V$		35	nS
Rise time	t_r	$I_C = 10mA, I_{B1} = -I_{B2} = 1mA$		35	nS
Storage time	t_s	$V_{CC} = 3V, I_C = 10mA$		200	nS
Fall time	t_f	$I_{B1} = -I_{B2} = 1mA$		50	nS

MAXIMUM RATINGS(Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Collector Power Dissipation	0.2	W
T _J	Junction Temperature	150	℃
T _{stg}	Storage Temperature	-55-150	℃

PNP 3906 ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.05	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-0.1mA	60			
	h _{FE(2)}	V _{CE} =-1V, I _C =-1mA	80			
	h _{FE(3)}	V _{CE} =-1V, I _C =-10mA	100		300	
	h _{FE(4)}	V _{CE} =-1V, I _C =-50mA	60			
	h _{FE(5)}	V _{CE} =-1V, I _C =-100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10mA, I _B =-1mA			-0.25	V
	V _{CE(sat)2}	I _C =-50mA, I _B =-5mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =-10mA, I _B =-1mA	-0.65		-0.85	V
	V _{BE(sat)2}	I _C =-50mA, I _B =-5mA			-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	250			MHz
Collector output capacitance	C _{ob}	V _{CB} =-5V, I _E =0, f=1MHz			4.5	pF
Noise figure	NF	V _{CE} =-5V, I _C =-0.1mA, f=1KHz, R _g =1KΩ			4	dB
Delay time	t _d	V _{CC} =-3V, V _{BE} =-0.5V			35	nS
Rise time	t _r	I _C =-10mA, I _{B1} =-I _{B2} =-1mA			35	nS
Storage time	t _s	V _{CC} =-3V, I _C =-10mA			225	nS
Fall time	t _f	I _{B1} =-I _{B2} =-1mA			75	nS

Ordering information

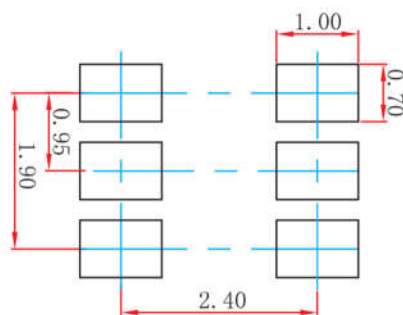
Package	Packing Description	Packing Quantity
SOT23-6L	Tape/Reel, 7" reel	3000PCS/Reel 120000PCS/Carton

Package Dimensions

SOT23-6L

Dim.	Millimeter(mm)		mil	
	Min.	Max.	Min.	Max.
A	1.05	1.25	41	49
A1	0	0.10	0	3.9
A2	1.05	1.15	41	45
b	0.30	0.50	11.8	19.7
c	0.10	0.20	3.9	7.9
D	2.82	3.02	111	119
E1	1.50	1.70	45	67
E	2.65	2.95	104	116
e	0.950(BSC)		37(BSC)	
e1	1.80	2.00	71	79
L	0.30	0.60	11.8	23.6
θ	0°	8°	0°	8°

The recommended mounting pad size



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